BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L

General Purpose Transistors

NPN Silicon

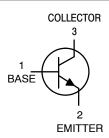
Features

- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	45	V
Collector - Base Voltage	V_{CBO}	50	V
Emitter – Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	Ic	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.



SOT-23 CASE 318 STYLE 6

MARKING DIAGRAM



6x = Device Code x = A, B, or C

M = Date Code*= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		I		1	
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	V _(BR) CEO	45	_	_	V
Collector – Emitter Breakdown Voltage $(V_{EB}=0,I_C=10\mu\text{A})$	V _{(BR)CES}	50	_	-	V
Emitter – Base Breakdown Voltage (I _E = 1.0 μA)	V _{(BR)EBO}	5.0	_	-	V
Collector Cutoff Current (V _{CB} = 20 V) (V _{CB} = 20 V, T _A = 150°C)	I _{CBO}	- -	_ _	100 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain $ (I_C = 100 \text{ mA}, \text{ V}_{CE} = 1.0 \text{ V}) \\ \text{BC817-16, SBC817-16} \\ \text{BC817-25, SBC817-25} \\ \text{BC817-40, SBC817-40} \\ \text{(I}_C = 500 \text{ mA, V}_{CE} = 1.0 \text{ V}) $	h _{FE}	100 160 250 40	- - -	250 400 600 –	ı
Collector – Emitter Saturation Voltage (I _C = 500 mA, I _B = 50 mA)	V _{CE(sat)}		_	0.7	V
Base – Emitter On Voltage (I _C = 500 mA, V _{CE} = 1.0 V)	V _{BE(on)}	_	_	1.2	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)	f _T	100	_	-	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	-	10	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Specific Marking	Package	Shipping [†]	
BC817-16LT1G			0000 / Tarra 9 David	
NSVBC817-16LT1G		SOT-23	3000 / Tape & Reel	
BC817-16LT3G	6A	(Pb-Free)	10.000 / Table 9 Paul	
SBC817-16LT3G			10,000 / Tape & Reel	
BC817-25LT1G		SOT-23 (Pb-Free)	3000 / Tape & Reel	
SBC817-25LT1G	20			
BC817-25LT3G	6B		10.000 (T	
SBC817-25LT3G			10,000 / Tape & Reel	
BC817-40LT1G		SOT-23	3000 / Tape & Reel	
SBC817-40LT1G				
BC817-40LT3G	6C	(Pb-Free)	40.000 /Taba 0 Bask	
SBC817-40LT3G			10,000 / Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L

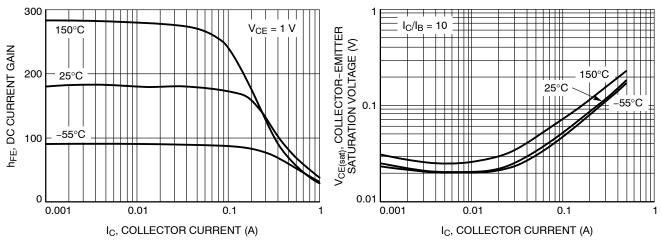


Figure 1. DC Current Gain vs. Collector Current

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

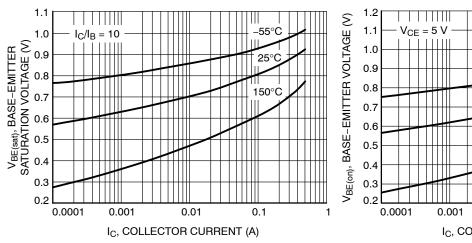


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

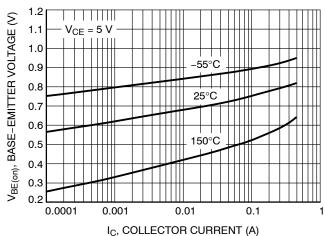
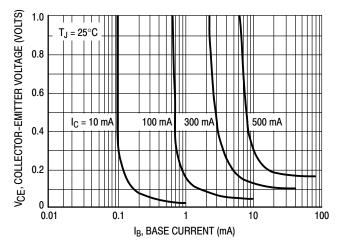


Figure 4. Base Emitter Voltage vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L



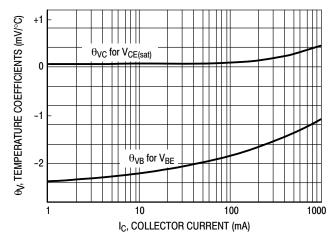


Figure 5. Saturation Region

Figure 6. Temperature Coefficients

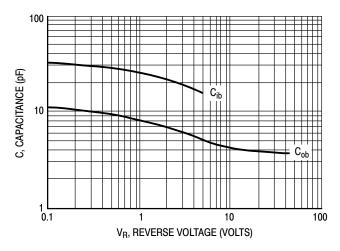


Figure 7. Capacitances

TYPICAL CHARACTERISTICS - BC817-25L, SBC817-25L

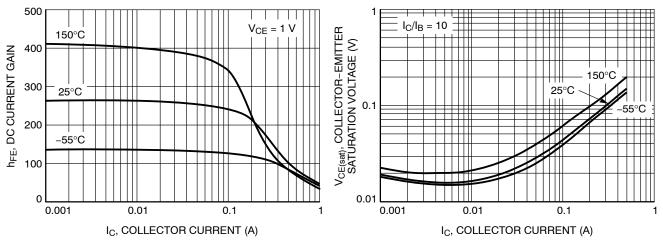


Figure 8. DC Current Gain vs. Collector Current

Figure 9. Collector Emitter Saturation Voltage vs. Collector Current

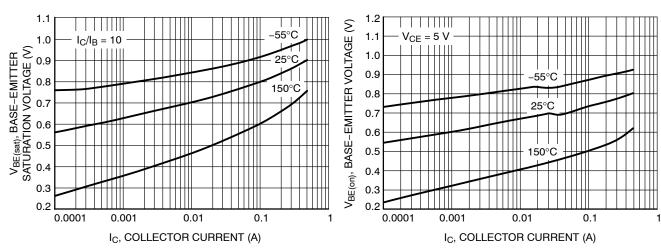


Figure 10. Base Emitter Saturation Voltage vs. Collector Current

Figure 11. Base Emitter Voltage vs. Collector Current

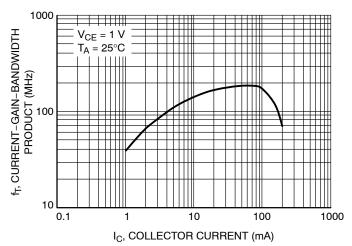
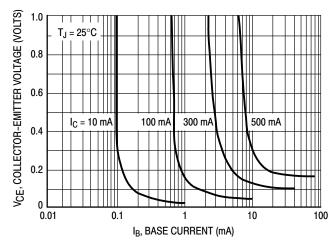


Figure 12. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-25L, SBC81725L



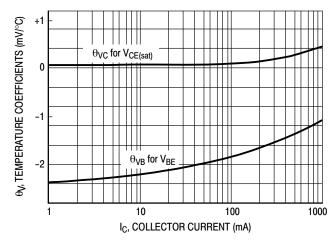


Figure 13. Saturation Region

Figure 14. Temperature Coefficients

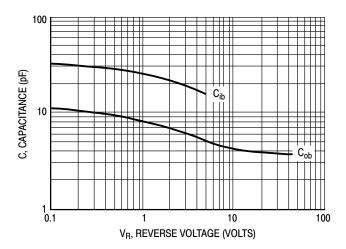


Figure 15. Capacitances

TYPICAL CHARACTERISTICS - BC817-40L, SBC817-40L

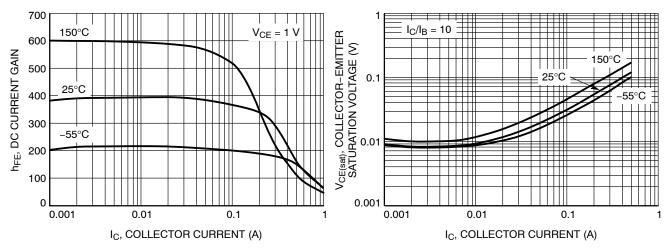


Figure 16. DC Current Gain vs. Collector Current

Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

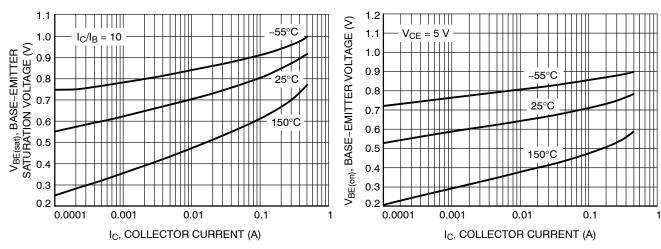


Figure 18. Base Emitter Saturation Voltage vs. Collector Current

Figure 19. Base Emitter Voltage vs. Collector Current

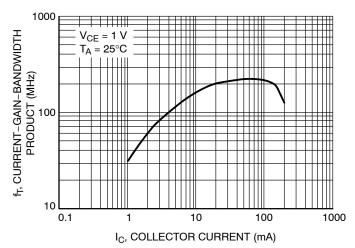
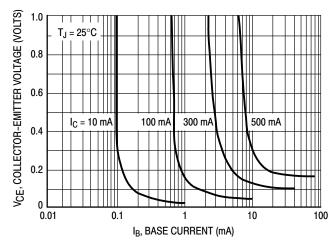


Figure 20. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-40L, SBC817-40L



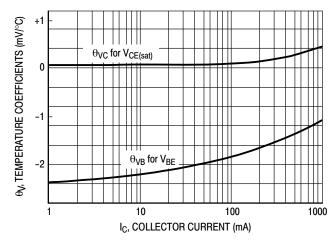


Figure 21. Saturation Region

Figure 22. Temperature Coefficients

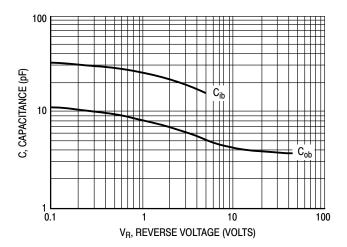


Figure 23. Capacitances

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L

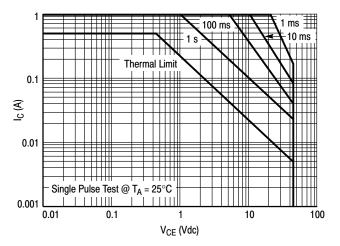


Figure 24. Safe Operating Area

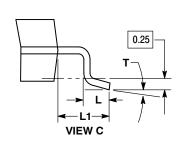


SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

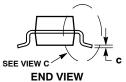
DATE 30 JAN 2018

SCALE 4:1 D - 3X b

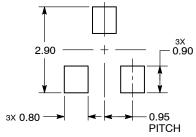
TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

3. ANODE

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	O٥		100	O٥		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	PIN 1. CATHODE 2. CATHODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE				

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